

Keisuke Shinohara

List of Publications by Year in descending order

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7
papers

463
citations

1937685
4
h-index

2053705
5
g-index

7
all docs

7
docs citations

7
times ranked

637
citing authors

#	ARTICLE	IF	CITATIONS
1	Scaling of GaN HEMTs and Schottky Diodes for Submillimeter-Wave MMIC Applications. IEEE Transactions on Electron Devices, 2013, 60, 2982-2996.	3.0	383
2	Novel Asymmetric Slant Field Plate Technology for High-Speed Low-Dynamic R _{on} E/D-mode GaN HEMTs. IEEE Electron Device Letters, 2017, 38, 95-98.	3.9	38
3	GaN-Based Field-Effect Transistors With Laterally Gated Two-Dimensional Electron Gas. IEEE Electron Device Letters, 2018, 39, 417-420.	3.9	31
4	III-Nitride millimeter wave transistors. Semiconductors and Semimetals, 2019, 102, 141-184.	0.7	4
5	<i>(Invited)</i> GaN-Based Multiple 2DEG Channel BRIDGE (Buried Dual Gate) HEMT Technology for High Power and Linearity. ECS Transactions, 2019, 92, 103-108.	0.5	4
6	Linearity Aspects of High Power Amplification in GaN Transistors. , 2020, , 83-107.		3
7	<i>(Invited)</i> GaN-Based Multiple 2DEG Channel BRIDGE (Buried Dual Gate) HEMT Technology for High Power and Linearity. ECS Meeting Abstracts, 2019, , .	0.0	0